

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listing of claims in the application.

**LISTING OF CLAIMS:**

1. (Currently Amended) A high frequency power amplification electric part comprising:
  - a power amplification circuit for amplifying a modulated high frequency signal;
  - a first transistor for detecting an output of the power amplification circuit by receiving a signal input to the power amplification circuit;
  - a current mirror circuit for generating a first current in proportion to a second current of the first transistor; and
  - a bias generating circuit for supplying a bias to said power amplification circuit in accordance with the first current,wherein a first capacitive element for transmitting variation of said output of said power amplification circuit is coupled between an output terminal of said power amplification circuit and a control terminal of a ~~third~~ second transistor included in said current mirror circuit for receiving the second current.
2. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein an impedance matching circuit and a second capacitive element for blocking direct current are coupled between said output terminal of said power amplification circuit and the output terminal, and one end of said first capacitive element is coupled to any one of nodes between said output terminal of the power amplification circuit and said second capacitive element.
3. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein said first transistor and said current mirror circuit are formed on a same semiconductor chip, the semiconductor chip and said power amplification circuit

are mounted on an insulating substrate, and said first capacitive element is constructed by a dielectric layer formed on said insulating substrate and a pair of conductive layers formed so as to sandwich the dielectric layer.

4. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein said first capacitive element has a capacitance value of at least 1 pF.

5. (Previously Presented) The high frequency power amplification electric part according to claim 1, further comprising a resistive element for converting the first current transferred from said current mirror circuit into a voltage.

6. (Currently Amended) The high frequency power amplification electric part according to claim 5, further comprising a comparing circuit for comparing the voltage obtained by conversion of said resistive element with an output level instruction signal and outputting a signal according to the difference of the voltage and the output level instruction signal, wherein the ~~bias~~-bias generating circuit generates said bias to said power amplification circuit in accordance with an output of the comparing circuit.

7. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein said power amplification circuit includes a field effect transistor, and the bias is supplied to the gate terminal of said field effect transistor.

8. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein said power amplification circuit has a plurality of amplifying stages coupled in cascade, a final stage of the plurality of amplifying stages is formed on a first semiconductor chip, the amplifying stages other than the final stage are formed on a second semiconductor chip, and said first transistor and said current mirror circuit are formed on a third semiconductor chip.

9. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein said power amplification circuit has a plurality of amplifying stages coupled in cascade, a final stage of the plurality of amplifying stages, said first transistor and said current mirror circuit are formed on a first semiconductor chip, and said amplifying stages other than the final stage are formed on a second semiconductor chip.

10. (Previously Presented) The high frequency power amplification electric part according to claim 1, wherein a resistive element is coupled between an input terminal of said power amplification circuit and a control terminal of said first transistor.

11. (Currently Amended) The high frequency power amplification electric part according to claim 1, wherein a resistive element is coupled between said first transistor and said ~~third~~ second transistor.

12. (Previously Presented) A wireless communication system comprising:  
a high frequency power amplification electric part according to claim 1;  
a second electric part having a transmission/reception switching circuit for switching between a transmission signal and a reception signal;  
a third electric part for modulating a signal to be transmitted and supplying the modulated signal to said high frequency power amplification electric part; and  
a semiconductor integrated circuit for supplying an output level instruction signal to said high frequency power amplification electric part.

13. (Original) The wireless communication system according to claim 12, wherein said high frequency power amplification electric part has a first power amplification circuit for amplifying a signal in a first frequency band and a second power amplification circuit for amplifying a signal in a second frequency band,

said second electric part has signal switching means for switching between a signal in the first frequency band and the signal in the second frequency band, and

said third electric part has a circuit for modulating the signal in the first frequency band and a circuit for modulating a signal in the second frequency band.

14. (Currently Amended) A high frequency power amplification electric part comprising:

~~a power amplification circuit having an output terminal for receiving a high frequency signal as an input signal and outputting a signal according to the input signal~~

a power amplification circuit having input and output terminals, the input terminal for receiving a high frequency signal as an input signal and outputting a signal according to the input signal;

a detecting circuit having a transistor for output detection which receives the input signal from the power amplification circuit, and forming an output signal according to said input signal;

a bias generating circuit for applying a bias according to the output signal of the detecting circuit to said power amplification circuit; and

a first capacitive element for transmitting fluctuation in said output terminal to said detecting circuit, which is connected between the output terminal of said power amplification circuit and said detecting circuit.

15. (Previously Presented) The high frequency power amplification electric part according to claim 14, wherein an impedance matching circuit and a second capacitive element for blocking direct current are connected between the output terminal of said power amplification circuit and a terminal to which an antenna is to be connected, and one of terminals of said first capacitive element is coupled between the output terminal of the power amplification circuit and said second capacitive element for blocking direct current.

16. (Previously Presented) A wireless communication system comprising:

a high frequency power amplification electric part according to claim 14;

a second electric part having a transmission/reception switching circuit for switching between a transmission signal and a reception signal;

a third electric part for modulating a signal to be transmitted and supplying the modulated signal to said high frequency power amplification electric part; and

a semiconductor integrated circuit for supplying an output level instruction signal to said high frequency power amplification electric part.